

<b>Notice of References Cited</b>	Application/Control No. 6693021	Applicant(s)/Patent Under Reexamination ISHIBASHI ET AL.	
	Examiner Savitri Mulpuri	Art Unit 2812	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-2002/0152952	10-2002	Beaumont et al.	117/95
*	B	US-6,693,021	02-2004	Motoki et al.	438/481
*	C	US-2002/0046693	04-2002	Kiyoku et al.	117/8
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	WO99/20816	04-1999	france	beaumont	
	O					
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	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	A twostp method for epitaxial lateral overgrowth of GaN(see conference article presented by Meaumont July 1999.3 <sup>rd</sup> internation conference on Nitride semiconductors Montpellier, france 4-9 July 1999.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.